

## TO-92MOD Plastic-Encapsulated Transistors

### 2SA1283 TRANSISTOR (PNP)

#### FEATURE

Power dissipation

$$P_{CM} : 0.9 \text{ W (Tamb=25°C)}$$

Collector current

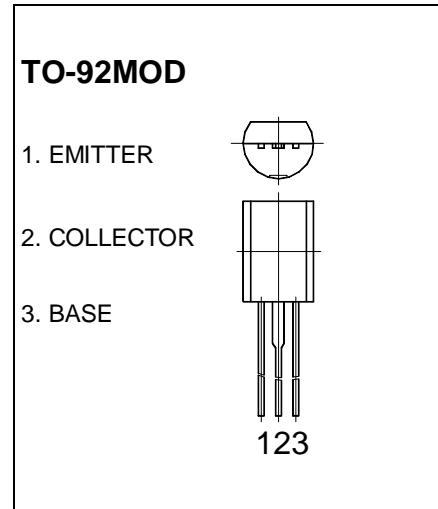
$$I_{CM} : -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-6		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50 V, I_E = 0$		-0.2	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4 V, I_C = 0$		-0.2	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -4 V, I_C = -100mA$	55	300	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = -500 mA, I_B = -25 mA$		-0.3	V
Transition frequency	$f_T$	$V_{CE} = -2V, I_C = -10mA$	50		MHz
Output capacitance	$C_{ob}$	$V_{CE} = -10V, I_E = 0, f = 1 \text{ MHz}$		25	pF

#### CLASSIFICATION OF $h_{FE}$

Rank	C	D	E
Range	55-110	90-180	150-300